

# INDEX

|                                                                                |     |
|--------------------------------------------------------------------------------|-----|
| 1 Introduction                                                                 | 13  |
| 2 Discrete semiconductor devices                                               | 21  |
| 2.1 Single-crystal semiconductor devices                                       | 21  |
| 2.1.1 MS and PN junction                                                       | 21  |
| 2.1.2 Devices containing one PN junction – diodes                              | 24  |
| 2.1.3 Bipolar transistors                                                      | 32  |
| 2.1.4 Basic BJT circuits                                                       | 36  |
| 2.1.5 Limit frequencies of bipolar transistors                                 | 41  |
| 2.1.6 Multilayer switching devices                                             | 43  |
| 2.1.7 Bulk-effect devices                                                      | 49  |
| 2.1.7.1 Unipolar transistors                                                   | 52  |
| 2.1.8 Surface effect-based devices                                             | 56  |
| 2.1.9 Submicron and heterogeneous devices                                      | 61  |
| 2.2 Polycrystalline semiconductor devices                                      | 65  |
| 2.2.1 Varistor                                                                 | 66  |
| 2.2.2 Thermistor and posistor                                                  | 67  |
| 2.3 Semiconductor optical devices                                              | 72  |
| 2.3.1 Single-crystal devices for detection and generation of optical radiation | 73  |
| 2.3.2 Polycrystalline optical radiation detectors                              | 80  |
| 2.3.3 Heterogeneous optical devices                                            | 82  |
| 2.4 Devices controlled by non-electrical quantities                            | 84  |
| 2.4.1 Special detectors of radiation                                           | 84  |
| 2.4.2 Magnetic field controlled devices                                        | 85  |
| 2.4.3 Thermocouples and cooling cells                                          | 87  |
| 2.4.4 Single-crystal temperature sensors                                       | 89  |
| 3 Vacuum tubes and discharge devices                                           | 91  |
| 3.1 Devices with density modulation of the electron beam                       | 92  |
| 3.1.1 Diode and triode                                                         | 92  |
| 3.1.2 Transmitting power tubes                                                 | 95  |
| 3.2 Velocity-modulated beam tubes                                              | 97  |
| 3.2.1 Utilization of non-zero transit time                                     | 97  |
| 3.2.2 Increasing interaction time                                              | 98  |
| 3.2.3 Magnetrons                                                               | 100 |
| 3.3 Optical tubes                                                              | 102 |
| 3.3.1 Picture tubes                                                            | 102 |
| 3.3.2 Optoelectronic converters                                                | 108 |
| 3.3.3 Image converters and intensifiers                                        | 110 |
| 3.4 Discharge tubes                                                            | 111 |
| 3.4.1 Devices based on discharge in gas                                        | 114 |
| 3.4.2 Glow-discharge tubes and fluorescents                                    | 114 |
| 4 Basic theory of circuits using discrete devices                              | 117 |
| 4.1 Important conventions used in electronic circuit analysis                  | 117 |

|                                                               |     |
|---------------------------------------------------------------|-----|
| 4.1.1 Operating points                                        | 119 |
| 4.2 Device response to signal variations                      | 124 |
| 4.2.1 Linearization of empirical characteristics              | 124 |
| 4.2.2 Linear equivalent circuit of a device                   | 128 |
| 4.2.2.1 LEC of a diode                                        | 129 |
| 4.2.2.2 LECs of bipolar transistors                           | 130 |
| 4.2.2.3 Giacoletto equivalent circuit of a bipolar transistor | 132 |
| 4.2.2.4 Unipolar transistor LEC                               | 134 |
| 4.2.3 Small-signal linear reactance equivalents               | 134 |
| 4.2.4 Large-signal reactance equivalents                      | 135 |
| 4.2.5 Bipolar transistor large-signal equivalent circuit      | 136 |
| 5 Basic applications of discrete devices                      | 139 |
| 5.1 Circuits with bipolar transistors                         | 139 |
| 5.1.1 Common emitter circuit                                  | 139 |
| 5.1.2 $P_o$ -stabilize CE amplifier stage                     | 142 |
| 5.1.3 Unbypassed emitter resistor                             | 142 |
| 5.1.4 Common collector stage                                  | 143 |
| 5.1.5 Common base circuit                                     | 145 |
| 5.1.6 LC-tuned CE amplifier                                   | 147 |
| 5.1.7 The Darlington amplifier                                | 148 |
| 5.1.8 Non-symmetrical phase inverter                          | 151 |
| 5.1.9 Symmetrical phase inverter                              | 152 |
| 5.2 Circuits with unipolar transistors                        | 152 |
| 5.2.1 Common source and common drain amplifier                | 153 |
| 5.2.2 Amplifier with enhancement-mode transistor              | 155 |
| 5.3 Power circuits with discrete transistors                  | 155 |
| 5.3.1 Amplifier classes                                       | 156 |
| 5.3.1.1 Class A                                               | 156 |
| 5.3.1.2 Class B                                               | 158 |
| 5.3.1.3 Class C                                               | 161 |
| 5.3.1.4 Class D                                               | 162 |
| 5.4 Switching devices                                         | 164 |
| 5.4.1 Applications of diodes                                  | 164 |
| 5.4.1.1 Half-wave rectifier                                   | 164 |
| 5.4.1.2 Full-wave rectifier                                   | 165 |
| 5.4.1.3 Calculation of ripple                                 | 166 |
| 5.4.2 Other applications of diodes                            | 169 |
| 5.4.2.1 Applications of varicaps                              | 167 |
| 5.4.2.2 Applications of photodiodes                           | 168 |
| 5.4.3 Multilayer switching devices                            | 168 |
| 5.4.3.1 Basic applications of thyristors                      | 169 |
| 5.4.3.2 Triac application                                     | 171 |
| 5.4.3.3 D.C. load control                                     | 172 |
| 5.5 Transistor power switches                                 | 174 |
| 5.5.1 Bipolar transistor operating as a switch                | 174 |
| 5.5.2 Unipolar switches                                       | 178 |
| 5.5.3 Combination structures                                  | 180 |
| 5.6 More advanced applications                                | 182 |

|           |                                                                     |     |
|-----------|---------------------------------------------------------------------|-----|
| 5.6.1     | Feedback                                                            | 182 |
| 5.6.2     | Oscillators                                                         | 182 |
| 5.6.2.1   | RC-tuned oscillators                                                | 183 |
| 5.6.2.1.1 | Free-running multivibrator                                          | 183 |
| 5.6.2.1.2 | Tunable low-frequency harmonic oscillator                           | 184 |
| 5.6.2.2   | LC-tuned oscillators                                                | 185 |
| 5.6.2.2.1 | Tunable H.F. oscillators                                            | 186 |
| 5.6.2.2.2 | Stable wide-frequency constant-amplitude oscillator                 | 186 |
| 5.6.2.3   | Crystal oscillators                                                 | 190 |
| 6         | Integrated circuits                                                 | 193 |
| 6.1       | Classification                                                      | 193 |
| 6.1.1     | Differences from discrete devices                                   | 196 |
| 6.1.2     | Basic structures                                                    | 196 |
| 6.1.2.1   | Bipolar transistors                                                 | 197 |
| 6.1.2.2   | Unipolar circuits                                                   | 201 |
| 6.1.2.3   | Mixed-technology structures                                         | 203 |
| 6.2       | Analog integrated circuits                                          | 204 |
| 6.2.1     | Operational amplifiers                                              | 204 |
| 6.2.2     | Inverting amplifier                                                 | 207 |
| 6.2.3     | Non-inverting amplifier                                             | 210 |
| 6.2.4     | Voltage follower                                                    | 210 |
| 6.2.5     | Superimposition of signals                                          | 211 |
| 6.2.6     | Time-dependent operations                                           | 212 |
| 6.2.7     | Nonlinear operations                                                | 213 |
| 6.2.7.1   | Logarithmic amplifiers                                              | 213 |
| 6.2.7.2   | Precision rectifier                                                 | 216 |
| 6.2.8     | Positive feedback                                                   | 217 |
| 6.3       | Internal functional blocks of monolithic analog integrated circuits | 219 |
| 6.3.1     | Quiescent operating point of a monolithic CE stage                  | 219 |
| 6.3.2     | Integrated differential amplifier                                   | 222 |
| 6.3.3     | Temperature compensated current source                              | 226 |
| 6.3.4     | Controlled differential amplifier                                   | 228 |
| 6.3.5     | Integrated power amplifiers                                         | 233 |
| 6.3.5.1   | Output stages                                                       | 234 |
| 6.3.5.2   | Input stages                                                        | 235 |
| 6.3.5.3   | Ground leads                                                        | 236 |
| 6.4       | Digital devices                                                     | 239 |
| 6.4.1     | TTL signal level standard                                           | 238 |
| 6.4.1.1   | Further bipolar devices                                             | 241 |
| 6.4.1.2   | ECL circuit family                                                  | 241 |
| 6.4.2     | Compatibility of digital IC families                                | 242 |
| 6.4.3     | Unipolar devices                                                    | 244 |
| 6.4.4     | Sequential devices                                                  | 244 |
| 6.4.5     | Flip-flops                                                          | 245 |
| 6.4.5.1   | The R-S flip-flop                                                   | 245 |
| 6.4.5.2   | The R-S-T flip-flop                                                 | 246 |

|                                          |     |
|------------------------------------------|-----|
| 6.4.5.3 The D-T flip-flop                | 246 |
| 6.4.6 Shift registers                    | 247 |
| 6.4.6.1 Two-phase dynamic shift register | 248 |
| 6.4.6.2 Static shift register            | 249 |
| 6.4.7 Charge-coupled structure (CCD)     | 251 |
| 6.4.8 Addressable memories               | 253 |
| 6.4.8.1 Bipolar static memory cell       | 255 |
| 6.4.8.2 Unipolar static memory cell      | 256 |
| 6.4.8.3 Dynamic unipolar memory cell     | 256 |
| 6.5 Mixed-mode devices                   | 257 |
| 6.6 Hybrid integrated circuits           | 260 |
| Appendix A: Passive components (review)  | 261 |
| A.1 Functional types                     | 261 |
| A.2 Sets of standard values              | 261 |
| A.3 Resistors                            | 263 |
| A.3.1 Equivalent circuit                 | 263 |
| A.3.2 Technological resistor types       | 264 |
| A.3.3 Variable resistors                 | 266 |
| A.3.4 Load capacity of resistors         | 267 |
| A.4 Capacitors                           | 267 |
| A.4.1 Variable capacitors                | 268 |
| A.5 Inductors                            | 268 |
| A.6 Color coding of component values     | 272 |
| A.7 Surface mounted devices              | 274 |
| References                               | 277 |